

High-Speed CMOS Logic Quad 2-Input NAND Gate with Open Drain

Features

- Buffered Inputs
- Typical Propagation Delay: 8ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Output Pull-up to 10V
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

The 'HC03 and 'HCT03 logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The HCT logic family is functionally as well as pin compatible with the standard LS logic family.

These open drain NAND gates can drive into resistive loads to output voltages as high as 10V. Minimum values of R_L required versus load voltage are shown in Figure 2.

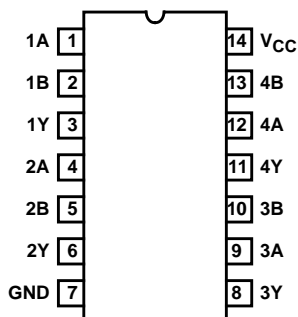
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC03F3A	-55 to 125	14 Ld CERDIP
CD54HCT03F3A	-55 to 125	14 Ld CERDIP
CD74HC03E	-55 to 125	14 Ld PDIP
CD74HC03M	-55 to 125	14 Ld SOIC
CD74HC03MT	-55 to 125	14 Ld SOIC
CD74HC03M96	-55 to 125	14 Ld SOIC
CD74HCT03E	-55 to 125	14 Ld PDIP
CD74HCT03M	-55 to 125	14 Ld SOIC
CD74HCT03MT	-55 to 125	14 Ld SOIC
CD74HCT03M96	-55 to 125	14 Ld SOIC

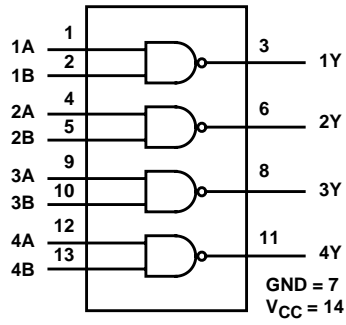
NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel. The suffix T denotes a small-quantity reel of 250.

Pinout

CD54HC03, CD54HCT03
(CERDIP)
CD74HC03, CD74HCT03
(PDIP, SOIC)
TOP VIEW



Functional Diagram



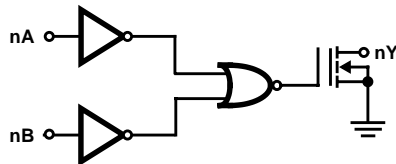
TRUTH TABLE

A	B	Y	
L	L	Z (Note 1)	H (Note 2)
H	L	Z (Note 1)	H (Note 2)
L	H	Z (Note 1)	H (Note 2)
H	H	L	L

NOTES:

1. Without pull-up (high impedance)
2. Requires pull-up (R_L to V_L)

Logic Symbol



CD54HC03, CD74HC03, CD54HCT, CD74HCT03

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O$	$-25mA$
DC V_{CC} or Ground Current, I_{CC} or I_{GND}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
E (PDIP) Package	80
M (SOIC) Package	86
Maximum Junction Temperature (Hermetic Package or Die) . . .	175°C
Maximum Junction Temperature (Plastic Package)	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I , V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS	
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX		
HC TYPES													
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V	
			0.02	6	-	-	0.1	-	0.1	-	0.1	V	
-			-	-	-	-	-	-	-	-	-	V	
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V	
			5.2	6	-	-	0.26	-	0.33	-	0.4	V	
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	2	-	20	-	40	μA	
HCT TYPES													
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V	
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V	

CD54HC03, CD74HC03, CD54HCT03, CD74HCT03

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} and GND	-	5.5	-		±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	2	-	20	-	40	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 4)	V _{CC} - 2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nA, nB	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, Input to Output (Figure 1)	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	100	-	125	-	150	ns
			4.5	-	-	20	-	25	-	30	ns
			6	-	-	17	-	21	-	26	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	8	-	-	-	-	ns	
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	18	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C _I	-	-	-	10	-	10	-	10	pF	
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	-	6.4	-	-	-	-	pF	
HCT TYPES											
Propagation Delay, Input to Output (Figure 1)	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	-	24	-	30	-	36	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	9	-	-	-	-	ns	
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C _I	-	-	-	10	-	10	-	10	pF	

CD54HC03, CD74HC03, CD54HCT03, CD74HCT03

Switching Specifications Input $t_r, t_f = 6\text{ns}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	-	9	-	-	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per gate.
- $P_D = C_{PD} V_{CC}^2 f_i + \sum (C_L V_{CC}^2 f_o) + \sum (V_L^2/R_L)$ (Duty Factor "Low")
 where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, V_{CC} = supply voltage, Duty Factor "Low" = percent of time output is "low", V_L = output voltage, R_L = pull-up resistor.

Test Circuits and Waveforms

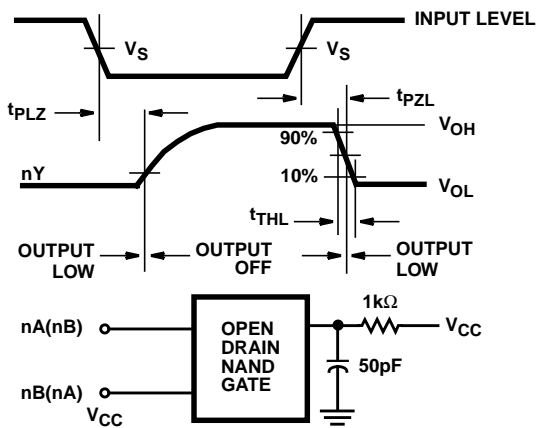


FIGURE 1. TRANSITION TIMES, PROPAGATION DELAY TIMES, AND TEST CIRCUIT

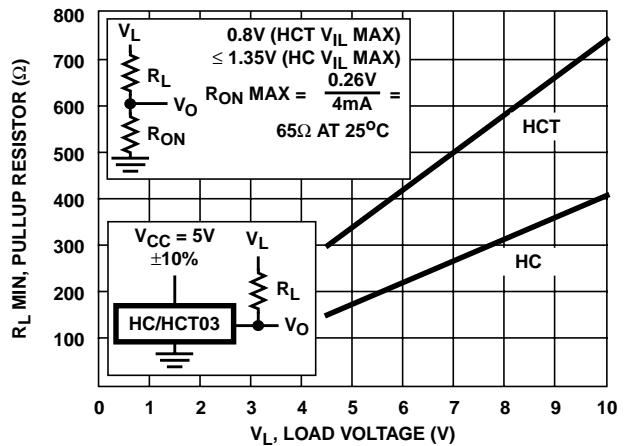


FIGURE 2. MINIMUM RESISTIVE LOAD vs LOAD VOLTAGE

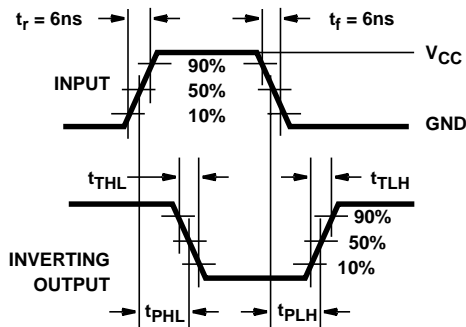


FIGURE 3. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

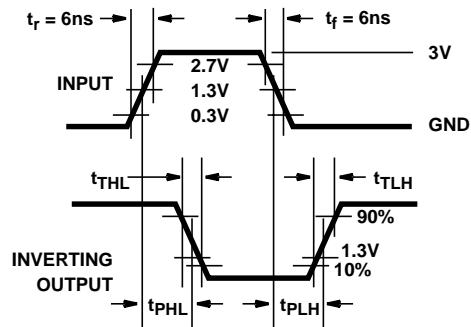


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC